

# Outline

- Module 5
  - Reducing supply voltage
  - Multiple supply voltages
  - Dynamic voltage scaling

**5.E Scaling Supplies** 

## Power /Energy Optimization Space

	Constant Throughpu	ut/Latency Variable The		oughput/Latency	
Energy	Design Time	Sleep Mode		Run Time	
Active	Logic design Scaled V <sub>DD</sub> Trans. sizing Multi-V <sub>DD</sub>	Clock gating		DFS, DVS	
Leakage	Stack effects Trans sizing Scaling V <sub>DD</sub> + Multi-V <sub>Th</sub>	Slee Multi-V <sub>DD</sub> + Input con	ep T's Variable V <sub>Th</sub> trol	DVS Variable V <sub>Th</sub>	

# Parallel Datapath



- The clock rate can be reduced by half with the same  $\begin{array}{l} \text{throughput} \Rightarrow f_{par} = f_{ref}/2 \\ \text{$\forall$ p_{ar} = V_{ref} / 1.7, C_{par} = 2.15C_{ref}$} \\ \text{$P_{par} = (2.15C_{ref}) (V_{ref}/1.7)^2 (f_{ref}/2) \approx 0.36 P_{ref}$} \end{array}$

• T. Burd, et al, JSSC, Nov 2000.



**Reference Datapath** 

Architecture Trade-off for Fixed-rate Processing



- Critical path delay  $\Rightarrow$  T<sub>adder</sub> + T<sub>comparator</sub> (= 25ns)  $\Rightarrow f_{ref} = 40 Mhz$
- Total capacitance being switched =  $C_{ref}$
- $V_{dd} = V_{ref} = 5V$
- Power for reference datapath =  $P_{ref} = C_{ref} V_{ref}^2 f_{ref}$ from [Chandrakasan92] (IEEE JSSC)

### **Pipelined Datapath**



- Critical path delay is less  $\Rightarrow$  max  $[T_{adder}, T_{comparator}]$
- Keeping clock rate constant:  $f_{pipe} = f_{ref}$ Voltage can be dropped  $\Rightarrow V_{pipe} = V_{ref} / 1.7$
- Capacitance slightly higher:  $C_{pipe} = 1.15C_{ref}$
- - $P_{pipe} = (1.15C_{ref}) (V_{ref}/1.7)^2 f_{ref} \approx 0.39 P_{ref}$



A Simple Datapath: Summary

Architecture type	Voltage	Area	Power
Simple datapath (no pipelining or parallelism)	5V	1	1
Pipelined datapath	2.9V	1.3	0.39
Parallel datapath	2.9V	3.4	0.36
Pipeline-Parallel	2.0V	3.7	0.2

Power /Energy Optimization Space

Variable Throughput/Latency

Run Time

DFS, DVS

DVS

Variable V<sub>Th</sub>

Sleep Mode

Clock gating

Sleep T's

Multi-V<sub>DD</sub> Variable V<sub>Th</sub>

Input control

Constant Throughput/Latency

Design Time

Logic design Scaled  $V_{\text{DD}}$ 

Trans. sizing

Multi-V<sub>DD</sub>

Stack effects Trans sizing

Scaling  $V_{\text{DD}}$ 

+ Multi-V<sub>Th</sub>



**5.F Multiple Supplies** 

### Multiple Supply Voltages

### • Block-level supply assignment

- ${}^{\bullet}$  Higher throughput/lower latency functions are implemented in higher  $V_{\rm DD}$
- Slower functions are implemented with lower  $V_{DD}$
- Often called "Voltage islands"
- Separate supply grids, level conversion performed at block boundaries
- Multiple supplies inside a block ("power domains" or "voltage islands")
  - Non-critical paths moved to lower supply voltage
  - Level conversion within the block • Physical design challenging

# **Power Domains**

Energy

Active

Leakage

### **Practical Examples**

### • Intel Skylake (ISSCC'16)

• Four power planes indicated by colors





### **Practical Examples**

• Intel 28-core Skylake-SP (ISSCC'18)



- Vcc: core supply (per core) ■} Vccclm: Un-core supply Vccsa: System Agent supply
- Vccio: Infrastructure supply
- Vccsfr: PLL supply } Vccddrd: DDR logic supply
  } Vccddra: DDR I/O supply

• 9 primary VCC domains are partitioned into 35 VCC planes

- Leakage Issue
  - $\bullet$  Driving from  $V_{\text{DDL}}$  to  $V_{\text{DDH}}$
- > Level converter









### Multiple Supplies Within A Block

• Downsizing, lowering the supply on the critical path will lower the operating frequency

- Downsize (lowering supply) non-critical paths
  - Narrows down the path delay distribution
  - Increases impact of variations



FF

188

FF

FF

Multiple Supplies in a Block

Level-Converting Flip-Flop







Layout:







5.F Dynamic Voltage Scaling

Power /Energy Optimization Space								
		Constant Throughput/Latency Variable T nergy Design Time Sleep Mode		Variable Throughput/Latency				
	Energy			p Mode	Run Time			
	Active	Logic design Scaled V <sub>DD</sub> Trans. sizing Multi-V <sub>DD</sub>	Clock gating		DFS, DVS			
	Leakage	Stack effects Trans sizing Scaling V <sub>DD</sub> + Multi-V <sub>Th</sub>	Sleep T's Multi-V <sub>DD</sub> Variable V <sub>Th</sub> + Input control		DVS Variable V <sub>Th</sub>			





Exploit Data Dependent Computation Times To Vary the Supply

from [Nielsen94] (IEEE Transactions on VLSI Systems)









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- · Circuit design constraints. (Functional verification)
- · Circuit delay variation. (Timing verification)
- · Noise margin reduction. (Power grid, coupling)
- · Delay sensitivity. (Local power distribution)

Design verification complexity similar to high-performance processor design @ fixed V<sub>DD</sub>







### Tracking with SRAM in Critical Path

### Mismatch between logic and SRAM





SRAM multiplictive replica



Design for Dynamically Varying VDD

- Static CMOS logic.
- Ring oscillator.

Niki, JSSC'11

- · Dynamic logic (& tri-state busses).
- · Sense amp (& memory cell).

Max. allowed  $|dV_{DD}/dt| \rightarrow$  Min. C<sub>DD</sub> = 100nF (0.6µm) Circuits continue to properly operate as  $\mathbf{V}_{\text{DD}}$  changes





Multiple Path Tracking

CORE CL

Path type

Cho, ISSCC'16

**Tunable delay** 

Polarity

TDC[15] TDC [14] ... TDC [0]



